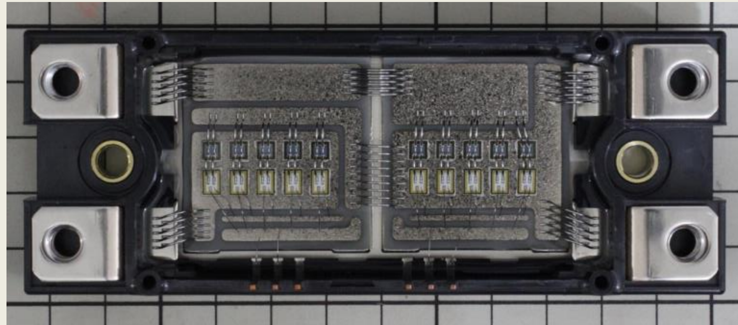
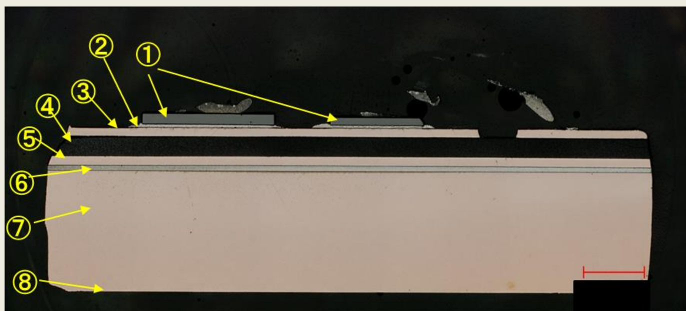
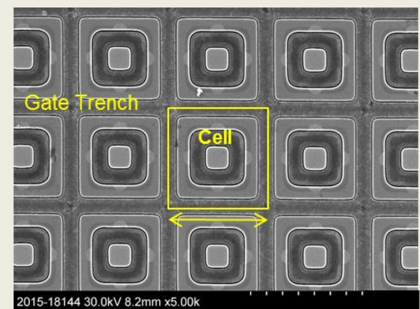
REPORT OF THE ROHM 3rd GENERATION SiC MOSFET POWER MODULE: BSM180D12P3C007



Overall appearance of the SiC Power module.



Cross-sectional view of the power module.



Top view of the Double Trench SiC MOSFET array.

- This 95 pages report reveals construction details of the ROHM-manufactured 180A, 1200V SiC half-bridge power module. 1) Module/Package structure, 2) 3rd Generation SiC MOSFET device featuring a Double-Trench structure.

- The report includes package details, layout analysis, die plane analysis by delayering technique, die cross sections (SEM), and materials analysis (EDX)

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